

## Siemens Power Hybrid for SMPS

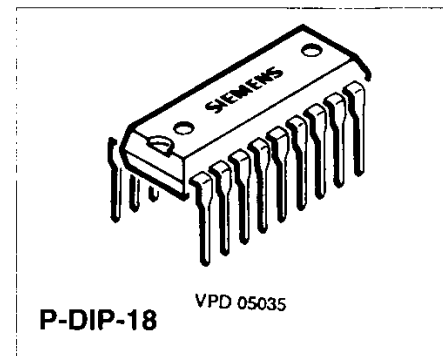
SPH 4690

Preliminary Data

Bipolar IC

### Features

- Fold-back characteristics provides overload protection for external components
- Burst operation under secondary short-circuit condition implemented
- Protection against open or a short of the control loop
- Switch-off if line voltage is too low (undervoltage switch-off)
- Line voltage depending compensation of foldback point
- Soft-start for quiet start-up without noise generated by the transformer
- Chip-over temperature protection implemented (thermal shutdown)
- On-chip ringing suppression circuit against parasitic oscillations of the transformer



### Power MOSFET

- $V_{DS} = 600\text{ V}$
- $R_{DS\text{ on}} = 2.0\ \Omega$
- Repetitive Avalanche

Type	Ordering Code	Package
SPH 4690	Q67000-A5068	P-DIP-18-1 (11-P)

The Siemens Power Hybrid SPH 4690 contains the SMPS IC TDA 4605-3 as well as the SIEMENS POWER MOSFET in a P-DIP-18 package.

The IC TDA 4605-3 controls the MOS-power transistor and performs all necessary control and protection functions in free running flyback converters. Because of the fact that a wide load range is achieved, this IC is applicable for consumer as well as industrial power supplies.

The serial circuit and primary winding of the flyback transformer are connected in series to the input voltage. During the switch-on period of the transistor, energy is stored in the transformer. During the switch-off period the energy is fed to the load via the secondary winding. By varying the switch-on time of the power transistor, the IC controls each portion of energy transferred to the secondary side such that the output voltage remains nearly independent of load variations. The required control information is taken from the input voltage during the switch-on period of the transistor and from a regulation winding during the switch off period. A new cycle will start if the transformer has transferred the stored energy completely into the load.

In the different load ranges the switched-mode power supply (SMPS) behaves as follows:

**No-load operation:**

The power supply is operating in the burst mode at typical 20 to 40 kHz. The output voltage can be a little bit higher or lower than the nominal value depending of the design of the transformer and the resistor of the control voltage divider.

**Nominal operation:**

The switching frequency is reduced with increasing load and decreasing AC-voltage.

The output voltage is only dependent on the load.

**Overload point:**

Maximal output power is available at this point of the output characteristic.

**Overload:**

The energy transferred per operation cycle is limited at the top. Therefore the output voltages declines by secondary overloading.

**Pin Configuration Control IC**

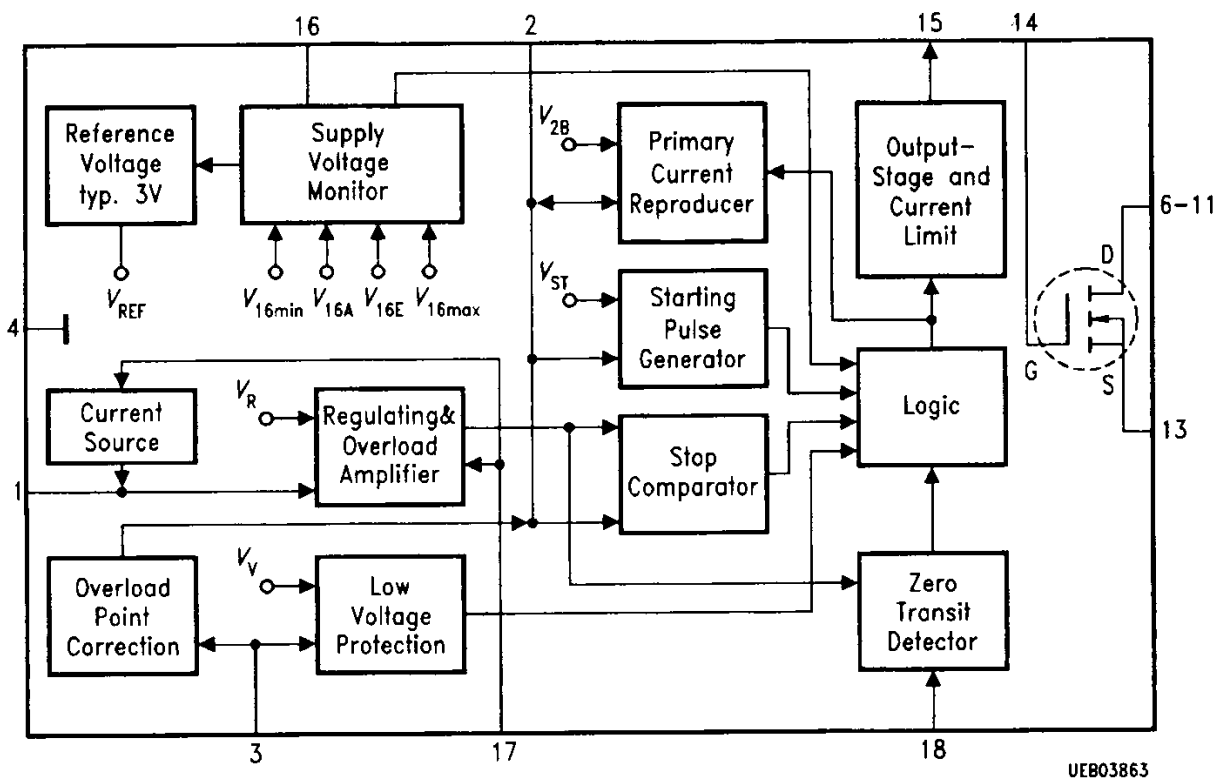
Pin 1	Regulating voltage
Pin 2	Primary current simulation
Pin 3	Primary voltage detector
Pin 4	Ground
Pin 15	Push-pull output
Pin 16	Supply voltage
Pin 17	Soft-Start
Pin 18	Zero detector

**Pin Configuration Power MOSFET**

Pin 5, 12	N.C.
Pin 6-11	MOSFET Drain
Pin 13	MOSFET Source
Pin 14	MOSFET Gate

## Pin Definitions and Functions

Pin No.	Function
1	<b>Information Input Concerning Secondary Voltage.</b> By comparing the regulating voltage - obtained from the regulating winding of the transformer - with the internal reference voltage, the output impulse width on pin 5 is adapted to the load of the secondary side (normal, overload, short circuit, no load).
2	<b>Information Input Regarding the Primary Current.</b> The primary current rise in the primary winding is simulated at pin 2 as a voltage rise by means of external RC-element. When a value is reached that's derived from the regulating voltage at pin 1, the output impulse at pin 5 is terminated. The RC-element serves to set the maximum power at the overload point set.
3	<b>Input for Primary Voltage Monitor.</b> When the line voltage is too low the IC is switched off by comparing $V_3$ with an internal reference. Voltage at pin 3 is used for overload point compensation. Overload point compensation will work 7 times the under voltage limit set.
4	<b>Ground</b>
5	Not connected
6-11	<b>MOSFET Drain</b>
12	Not connected
13	<b>MOSFET Source</b>
14	<b>MOSFET Gate</b>
15	<b>Output:</b> Push-pull output provides $\pm 1$ A for rapid charge and discharge of the gate capacitance of the power MOS transistor.
16	<b>Supply Voltage Input.</b> From it a stable internal reference voltage $V_{REF}$ and the switching thresholds $V_{6A}$ , $V_{6E}$ , $V_{6max}$ and $V_{6min}$ for the supply voltage detector is formed. If $V_6 > V_{6E}$ then $V_{REF}$ is switched on and switched off when $V_6 < V_{6A}$ . In addition the logic is only enabled for $V_{6min} > V_6$ .
17	<b>Input for Soft-Start.</b> Start up will begin with short pulses by connecting a capacitor from pin 7 to ground.
18	<b>Input for the Oscillation Feedback.</b> After starting oscillation, every zero transit of the feedback voltage (falling edge) triggers an output impulse at pin 5. The trigger threshold is at + 50 mV typical.



Block Diagram

## Circuit Description

### Application Circuit

The application circuit shows a flyback converter for video recorders with an output power rating of 70 W. The circuit is designed as a wide-range power supply for AC-line voltage of 180 to 264 V. The AC-input voltage is rectified by the bridge rectifier GR1 and smoothed by  $C_1$ . The NTC limits the rush-in current.

In the period before the switch-on threshold is reached the IC is supplied via resistor  $R_1$ ; during the start-up phase it uses the energy stored in  $C_2$ , under steady state conditions the IC receives its supply voltage from transformer winding  $n_1$  via diode D1. The switching transistor T1 is a BUZ 90. The parallel connected capacitor  $C_3$  and the inductance of primary winding  $n_2$  determine the system resonance frequency. The  $R_2$ - $C_4$ -D2 circuitry limits overshoot peaks, and  $R_{13}$  protects the gate of T1 against static charges.

During the conductive phase of the power transistor T1 the current rise in the primary winding depends on the winding inductance and the mains voltage. The network consisting of  $R_4$ - $C_5$  is used to create a model of the sawtooth shaped rise of the collector current. The resulting control voltage is fed into pin 2 of the IC. The RC-time constant given by  $R_4$ - $C_5$  must be designed that way that driving the transistor core into saturation is avoided.

The ratio of the voltage divider  $R_{10}/R_{11}$  is fixing a voltage level threshold. Below this threshold the switching power supply shall stop operation because of the low mains voltage. The control voltage present at pin 3 also determines the correction current for the foldback point. This current added to the current flowing through  $R_4$  and represents an additional charge to  $C_5$  in order to reduce the turn-on phase of T1. This is done to stabilize the fold-back point even under higher main voltages.

Regulation of the switched-mode power supply is via pin 1. The control voltage of winding  $n_1$  during the off period of T1 is rectified by D3, smoothed by  $C_6$  and stepped down at an adjustable ratio by  $R_5$ ,  $R_6$  and  $R_7$ . The  $R_8$ - $C_7$  network suppresses parasitic overshoots (transformer oscillation). The peak voltage at pin 2, and thus the primary peak current, is adjusted by the IC so that the voltage applied across the control winding, and hence the output voltages, are at the desired level.

When the transformer has supplied its energy to the load, the control voltage passes through zero. The IC detects the zero crossing via series resistors  $R_9$  connected to pin 18. But zero crossings are also produced by transformer oscillation after T1 has turned off if outputs is short circuited. Therefore the IC ignores zero crossings occurring within a specified period of time after T1 turn-off.

The capacitor  $C_8$  connected to pin 17 causes the power supply to be started with shorter pulses to keep the operating frequency outside the audible range during start-up.

On the secondary side, three output voltages are produced across winding  $n_3$  to  $n_5$  rectified by D4 to D6 and smoothed by  $C_9$  to  $C_{11}$ . Resistor  $R_{12}$  is used as a bleeder resistor. Fusable resistors  $R_{15}$  and  $R_{16}$  protect the rectifiers against short circuits in the output circuits, which are designed to supply only small loads.

## Block Circuit Diagram

Page 4 shows the block diagram of the IC, page 18 shows the most important waveforms of the SMPS in operation.

### Pin 1

The regulating voltage forwarded to this pin is compared with a stable internal reference voltage  $V_R$  in the **regulating and overload amplifier**. The output of this stage is fed to the stop comparator. If the control voltage is rather small at pin 1 an additional current is added by means of current source which is controlled according the level at pin 7. This additional current is virtually reducing the control voltage present at pin 1.

### Pin 2

A voltage proportional to the drain current of the switching transistor is generated there by the external RC-combination in conjunction with the **primary current transducer**. The output on this transducer is controlled by the logic and referenced to the internal stable voltage  $V_{2B}$ . If the voltage  $V_2$  exceeds the output voltage of the regulations amplifier, the logic is reset by the stop comparator and consequently the output of pin 5 is switched to low potential. Further inputs for the logic stage are the output for the **start impulse generator** with the stable reference potential  $V_{ST}$  and the **supply voltage motor**.

### Pin 3

The down divide primary voltage applied there stabilized the overload point. In addition the logic is disabled in the event of low voltage by comparison with the internal stable voltage  $V_V$  in the **primary voltage monitor** block.

### Pin 4

Ground

### Pin 15

In the output stage the output signals produced by the logic are shifted to a level suitable for MOS-power transistors.

### Pin 16

From the supply voltage  $V_6$  are derived a stable internal references  $V_{REF}$  and the switching threshold  $V_{6A}$ ,  $V_{6E}$ ,  $V_{6max}$  and  $V_{6min}$  for the **supply voltage monitor**. All references values ( $V_R$ ,  $V_{2B}$ ,  $V_{ST}$ ) are derived from  $V_{REF}$ . If  $V_6 > V_{VE}$ , the  $V_{REF}$  is switched on and switched off when  $V_6 < V_{6A}$ . In addition, the logic is released only for  $V_{6min} < V_6 < V_{6max}$ .

### Pin17

The output of the overload amplifier is connected to pin 7. A load on this output causes a reduction in maximal impulse duration. This function can be used to implement a soft start, when pin 7 is connected to ground by a capacitor.

## Pin 18

The zero detector controlling the logic block recognizes the transformer being discharged by positive to negative zero crossing of pin 8 voltage and enables the logic for a new pulse. Parasitic oscillations occurring at the end of a pulse cannot lead to a new pulse (double pulsing), because an internal circuit inhibits the zero detector for a finite time  $t_{UL}$  after the end of each pulse.

## Start-Up Behaviour

The start-up behaviour of the application circuit per page 16 is represented on page 18 for a line voltage barely above the lower acceptable limit time  $t_0$  the following voltages built up:

- $V_6$  corresponding to the half-wave charge current over  $R_1$
- $V_2$  to  $V_{2max}$  (typically 6.6 V)
- $V_3$  to the value determined by the divider  $R_{10}/R_{11}$ .

The current drawn by the IC in this case is less than 1.6 mA.

If  $V_6$  reaches the threshold  $V_{6E}$  (time point  $t_1$ ), the IC switches on the internal reference voltage. The current draw max. rises to 12 mA. The primary current-voltage reproducer regulates  $V_2$  down to  $V_{2B}$  and the starting impulse generator generates the starting impulses from time point  $t_5$  to  $t_6$ . The feedback to pin 8 starts the next impulse and so on. All impulses including the starting impulse are controlled in width by regulating voltage of pin 1. When switching on this corresponds to a short-circuit event, i.e.  $V_1 = 0$ . Hence the IC starts up with "short circuit impulses" to assume a width depending on the regulating voltage feedback (the IC operates in the overload range). The IC operates at the overload point. Thereafter the peak values of  $V_2$  decrease rapidly, as the starting attempt is aborted (pin 5 is switched to low). As the IC remains switched on,  $V_6$  further decreases to  $V_6$ . The IC switches off;  $V_6$  can rise again (time point  $t_4$ ) and a new start-up attempt begins at time point  $t_1$ . If the rectified alternating line voltage (primary voltage) collapses during load,  $V_3$  can fall below  $V_{3A}$ , as is happening at time point  $t_3$  (switch-on attempt when voltage is too low). The primary voltage monitor then clamps  $V_3$  to  $V_{3S}$  until the IC switches off ( $V_6 < V_{6A}$ ). Then a new start-up attempt begins at time point  $t_1$ .

### Regulation, Overload and No-Load Behaviour

When the IC has started up, it is operating in the regulation range. The potential at pin 1 typically is 400 mV. If the output is loaded, the regulation amplifier allows broader impulses ( $V_5 = H$ ). The peak voltage value at pin 2 increases up to  $V_{2S_{max}}$ . If the secondary load is further increased, the overload amplifier begins to regulate the pulse width downward. This point is referred to as the overload point of the power supply. As the IC supply voltage  $V_6$  is directly proportional to the secondary voltage, it goes down in accordance with the overload regulation behaviour. If  $V_6$  falls below the value  $V_{6_{min}}$ , the IC goes into burst operation. As the time constant of the half-wave charge-up is relatively large, the short-circuit power remains small. The overload amplifier cuts back to the pulse width  $t_{pk}$ . This pulse width must remain possible, in order to permit the IC to start-up without problems from the virtual short circuit, which every switching on with  $V_1 = 0$  represents. If the secondary side is unloaded, the loading impulses ( $V_5 = H$ ) become shorter. The frequency increases up to the resonance frequency of the system. If the load is further reduced, the secondary voltages and  $V_6$  increase. When  $V_6 = V_{6_{max}}$ , the logic is blocked. The IC converts to burst operation. This renders the circuit absolutely safe under no-load conditions.

### Behaviour when Temperature Exceeds Limit

An integrated temperature protection disables the logic when the chip temperature becomes too high. The IC automatically interrogates the temperature and starts as soon as the temperature decreases to permissible values.



**Absolute Maximum Ratings**

$T_A = -20$  to  $85$  °C

Parameter	Symbol	Limit Values			Unit	Remarks
		min.	typ.	max.		

**TDA 4605-3**

Voltage	pin 1	$V_1$	-0.3		3	V	Supply voltage
	pin 2	$V_2$	-0.3			V	
	pin 3	$V_3$	-0.3			V	
	pin 15	$V_{15}$	-0.3		$V_{16}$	V	
	pin 16	$V_{16}$	-0.3		20	V	
	pin 17	$V_{17}$	-0.3			V	
Current	pin 1	$I_1$			3	mA	$t_p \leq 50 \mu s; v \leq 0.1$ $t_p \leq 50 \mu s; v \leq 0.1$ $t_p \leq 50 \mu s; v \leq 0.1$
	pin 2	$I_2$			3	mA	
	pin 3	$I_3$			3	mA	
	pin 4	$I_4$	-1.5			A	
	pin 15	$I_{15}$	-0.5		1.5	A	
	pin 16	$I_{16}$			0.5	A	
	pin 17	$I_{17}$			3	mA	
	pin 18	$I_{18}$	-5		3	mA	
Junction temperature	$T_j$			125	°C		
Storage temperature	$T_{stg}$	-40		125	°C		

**Power MOSFET**

Drain current	$I_D$		0.52		A	$T_A = 25$ °C
Pulsed drain current	$I_{D\ pulse}$		4.4		A	$T_A = 25$ °C
Gate source voltage	$V_{GS}$		$\pm 20$		V	-
Power dissipation	$P_D$		1		W	$T_A = 25$ °C
Single pulse Avalanche Energy	$E_{AS}$		320		mJ	$I_D = 4.4$ A; $V_{DD} = 50$ V $R_{GS} = 25$ $\Omega$ ; $L = 30$ mH
Repetitive avalanche Energy	$E_{AR}$		8		mJ	limited by $T_j$
Avalanche current repet. or non-repet.	$I_{AR}$		4.4		A	limited by $T_{j\ max}$
Operat. temperature	$T_j$	-55		125	°C	
Storage temperature	$T_{stg}$	-40		125	°C	

## Absolute Maximum Ratings (cont'd)

### Operating Range

Parameter	Symbol	Limit Values			Unit	Remarks
		min.	typ.	max.		

### TDA 4605-3

Supply voltage	$V_6$	7.5		15.5	V	IC "on"
Ambient temperature	$T_A$	- 20		85	°C	
Heat resistance						
Junction to environment	$R_{thJ-E}$			100	K/W	
Junction to package	$R_{thJ-G}$			70	K/W	measured at pin 4

**Characteristics** $T_A = 25\text{ °C}$ ;  $V_S = 10\text{ V}$ 

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

**TDA 4605-3****Start -Up Hysteresis**

Start-up current	$I_{16\text{ E0}}$		0.6	0.8	mA	$V_{16} = V_{16\text{ E}}$	1
Switch-on voltage	$V_{16\text{ E}}$	11	12	13	V		1
Switch-off voltage	$V_{16\text{ A}}$	4.5	5	5.5	V		1
Switch-on current	$I_{16\text{ E1}}$		11		mA	$V_{16} = V_{16\text{ E}}$	1
Switch-off current	$I_{16\text{ A1}}$		10		mA	$V_{16} = V_{16\text{ A}}$	1

**Voltage Clamp ( $V_6 = 10\text{ V}$ , IC switch-off)**

At pin 2 ( $V_{16} < V_{16\text{ E}}$ )	$V_{2\text{ max}}$	5.6	6.6	8	V	$I_2 = 1\text{ mA}$	1
At pin 3 ( $V_{16} < V_{16\text{ E}}$ )	$V_{3\text{ max}}$	5.6	6.6	8	V	$I_3 = 1\text{ mA}$	1

**Control Range**

Control input voltage	$V_{1\text{ R}}$	390	400	410	mV		2
Voltage gain of the control circuit in the control range	$-V_{\text{R}}$		43		dB	$V_{\text{R}} = d(V_{2\text{ S}} - V_{2\text{ B}})/dV_1$ $f = 1\text{ kHz}$	2

**Primary Current Simulation Voltage**

Basic value	$V_{2\text{ B}}$	0.97	1.00	1.03	V		2
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**Overload Range and Short Circuit Operation**

Peak value in the range of secondary overload	$V_{2\text{ B}}$	2.9	3.0	3.1	V	$V_1 = V_{1\text{ R}} - 10\text{ mV}$	2
Peak value in the range of secondary short circuit operation	$V_{2\text{ K}}$	2.2	2.4	2.9	V	$V_1 = 0$	2

**Foldback Point Correction**

Foldback point correction current	$-I_2$	300	500	650	$\mu\text{A}$	$V_3 = 3.7\text{ V}$	1
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**Characteristics (cont'd)** $T_A = 25\text{ °C}$ ;  $V_S = 10\text{ V}$ 

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

**Generally Valid Data ( $V_{16} = 10\text{ V}$ )****Voltage of the Zero Transition Detector**

Positive clamping	$V_{18P}$		0.75		V	$I_{18} = 1\text{ mA}$	2
Negative clamping	$V_{18N}$		-0.2		V	$I_{18} = 1\text{ mA}$	2
Threshold value	$V_{18S}$	40	50		mV		2
Suppression of transformer ringing	$t_{UL}$	3.0	3.4	3.8	$\mu\text{s}$		2
Input current	$-I_{18}$	0		4	$\mu\text{A}$	$V_{18} = 0$	

**Push-Pull Output Stage**

Saturation voltages:							
Pin 15 sourcing	$V_{Sat0}$		1.5	2.0	V	$I_{15} = -0.1\text{ A}$	1
Pin 15 sinking	$V_{SatV}$		1.0	1.2	V	$I_{15} = +0.1\text{ A}$	1
Pin 15 sinking	$V_{SatV}$		1.4	1.8	V	$I_{15} = +0.5\text{ A}$	1

**Output Slew Rate**

Rising edge	$+dV_{15}/dt$		70		V/ $\mu\text{s}$	-	2
Falling edge	$-dV_{15}/dt$		100		V/ $\mu\text{s}$	-	2

**Reduction of Control Voltage**

Current reduce the control voltage	$-I_1$		50		$\mu\text{A}$	$V_{17} = 1.1\text{ V}$	
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**Characteristics (cont'd)** $T_A = 25\text{ °C}$ ;  $V_S = 10\text{ V}$ 

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

**Protection Circuit**

Undervoltage protection for $V_6$ : voltage at pin 5 = $V_{15\text{ min}}$ if $V_{16} < V_{16\text{ min}}$	$V_{16\text{ min}}$	7.0	7.25	7.5	V		2
Undervoltage protection for $V_6$ : voltage at pin 15 = $V_{15\text{ min}}$ if $V_{16} > V_{16\text{ max}}$	$V_{16\text{ max}}$	15.5	16	16.5	V		2
Undervoltage protection for $V_{ac}$ : voltage at pin 15 = $V_{15\text{ min}}$ if $V_3 < V_{3A}$	$V_{3A}$	985	1000	1015	mV	$V_2 = 0\text{ V}$	1
Over temperature: at the given chip temperature the IC will switch $V_{15}$ to $V_{15\text{ min}}$	$T_j$		150		°C		2
Voltage at pin 3 if one of the protection function was triggered; ( $V_3$ will be clamped until $V_{16} < V_{16A}$ )	$V_{3\text{ Sat}}$		0.4	0.8	V	$I_3 = 750\text{ }\mu\text{A}$	1
Current drain during burst operation	$I_{16}$		8		mA	$V_3 = V_2 = 0\text{ V}$	1

**Characteristics (cont'd)**

$T_A = 25\text{ °C}; V_S = 10\text{ V}$

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			

**Power MOSFET**

**Static Ratings**

Drain source breakdown voltage	$V_{BR\ DSS}$	600			V	$V_{GS} = 0\text{ V};$ $I_D = 0.25\text{ mA}$	
Gate threshold voltage controlled by TDA 4605-3	$V_{GS\ th}$	2.1	3.0	4.0	V	$V_{GS} = V_{DS};$ $I_D = 1\text{ mA}$	
Zero gate voltage drain current	$I_{DSS}$		0.1	1.0	$\mu\text{A}$	$T_J = 25\text{ °C}$ $V_{DS} = 600\text{ V}$ $V_{GS} = 0\text{ V}$	
Zero gate voltage drain current	$I_{DSS}$		10	100	$\mu\text{A}$	$T_J = 125\text{ °C}$ $V_{DS} = 600\text{ V}$ $V_{GS} = 0\text{ V}$	
Drain source on state resistance	$R_{DS\ on}$			2.0	$\Omega$		

**Dynamic Ratings**

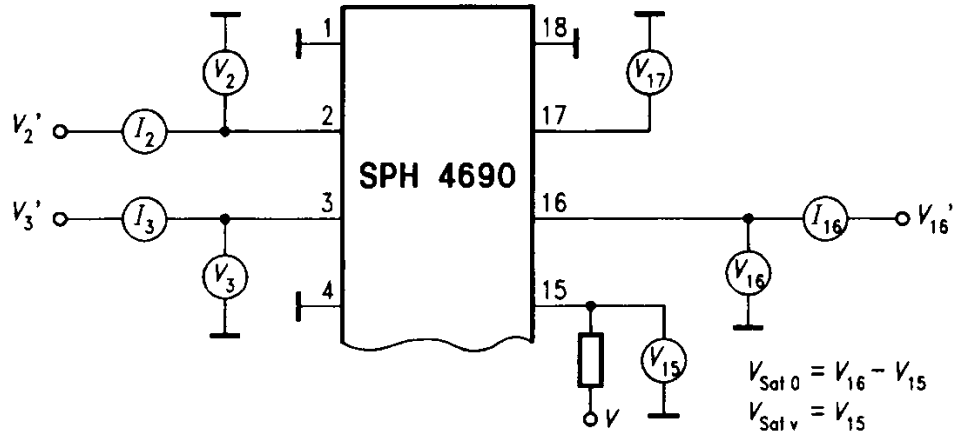
Forward transconductance	$g_{fs}$	2.5	3.8		S	$V_{DS} =$ $2 \times I_D \times R_{DS\ (on)\ max}$ $I_D = 2.8\text{ A}$	
Input capacitance	$C_{iss}$		780	1050	pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$	
Output capacitance	$C_{oss}$		110	170	pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$	
Reverse transfer capacitance	$C_{rs}$		40	70	pF	$V_{GS} = 0\text{ V}$ $V_{DS} = 25\text{ V}$ $f = 1\text{ MHz}$	
Turn-on delay time	$t_{d\ on}$		20	30	ns	$V_{CC} = 300\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 2.5\text{ A}$ $R_{GS} = 50\ \Omega$	

**Characteristics (cont'd)** $T_A = 25\text{ °C}; V_S = 10\text{ V}$ 

Parameter	Symbol	Limit Values			Unit	Test Condition	Test Circuit
		min.	typ.	max.			
Rise time	$t_r$		50	75	ns	$V_{CC} = 300\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 2.5\text{ A}$ $R_{GS} = 50\text{ }\Omega$	
Turn-off delay time	$t_{d\text{ off}}$		120	150	ns	$V_{CC} = 300\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 2.5\text{ A}$ $R_{GS} = 50\text{ }\Omega$	
Fall time	$t_f$		70	90	ns	$V_{CC} = 300\text{ V}$ $V_{GS} = 10\text{ V}$ $I_D = 2.5\text{ A}$ $R_{GS} = 50\text{ }\Omega$	

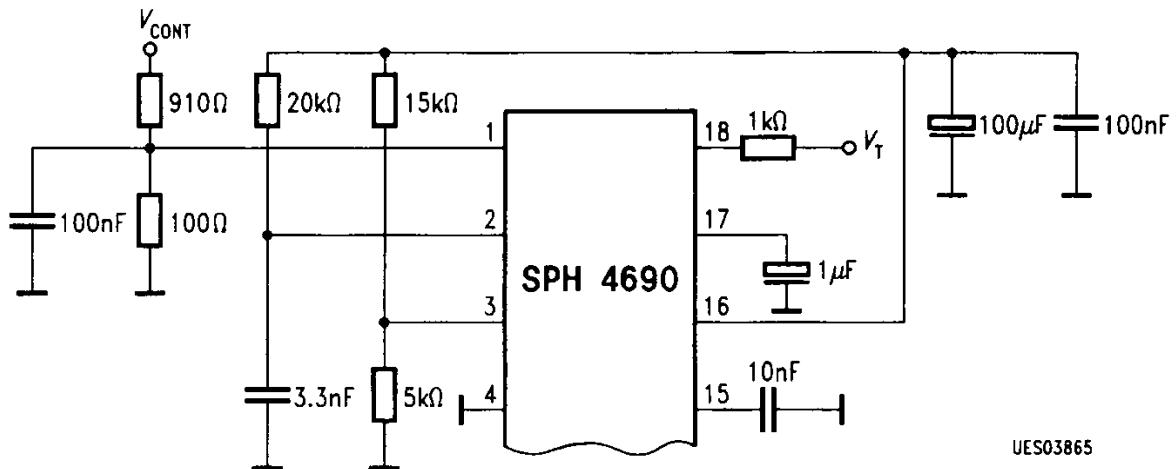
**Reverse Diode**

Continuous reverse drain current	$I_S$		0.55		A		
Pulsed reverse drain current	$I_{SM}$		4.4		A		
Diode forward	$V_{SD}$		1.0	1.2	V	$V_{GS} = 0\text{ V}$ $I_F = 2.8\text{ A}$	
Reverse recovery time	$t_{rr}$		350		ns	$V_R = 100\text{ V}$ $I_F = 2.8\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$	
Reverse recovery charge	$Q_{rr}$		2.5		$\mu\text{C}$	$V_R = 100\text{ V}$ $I_F = 2.8\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$	



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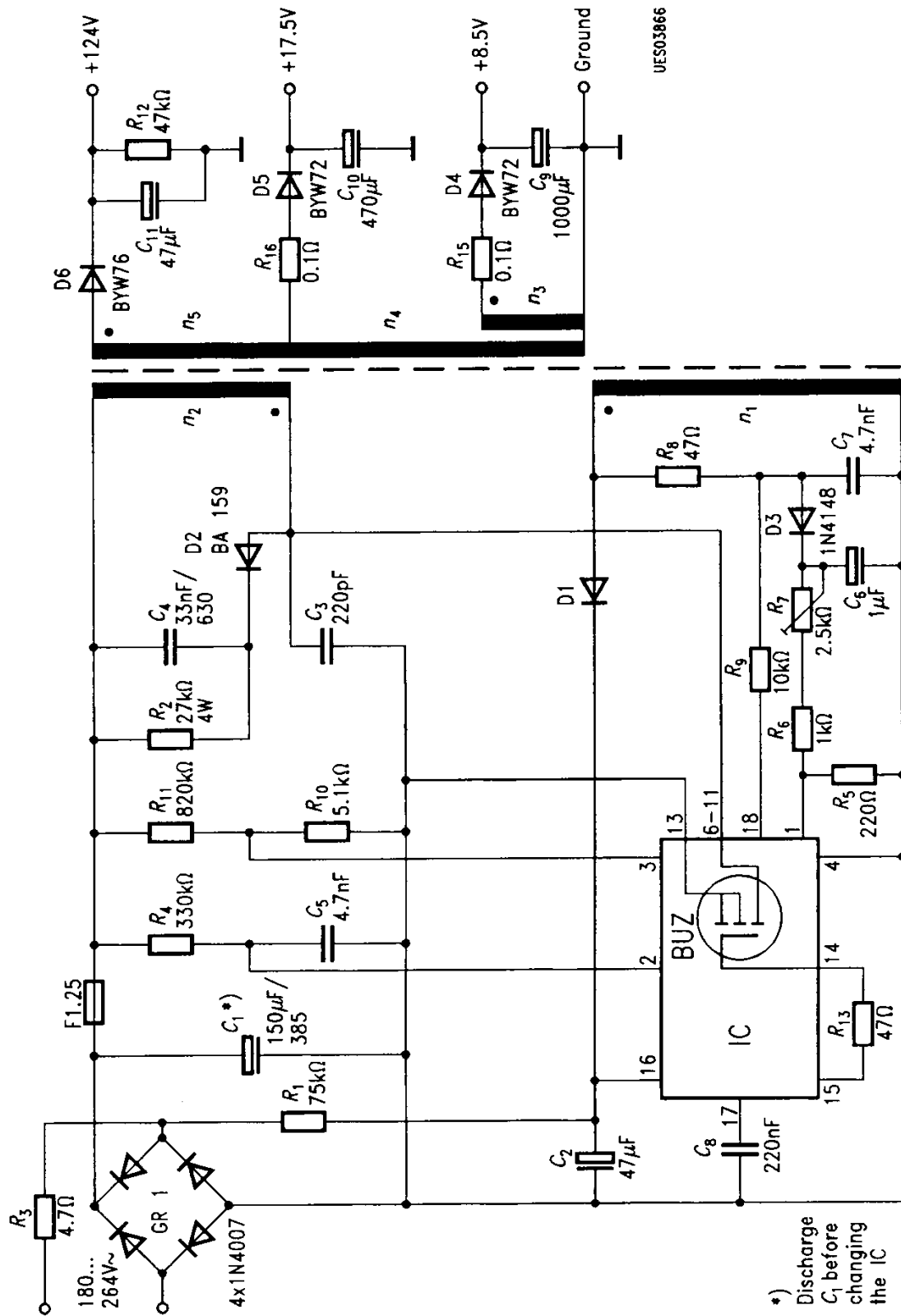
Test Circuit 1



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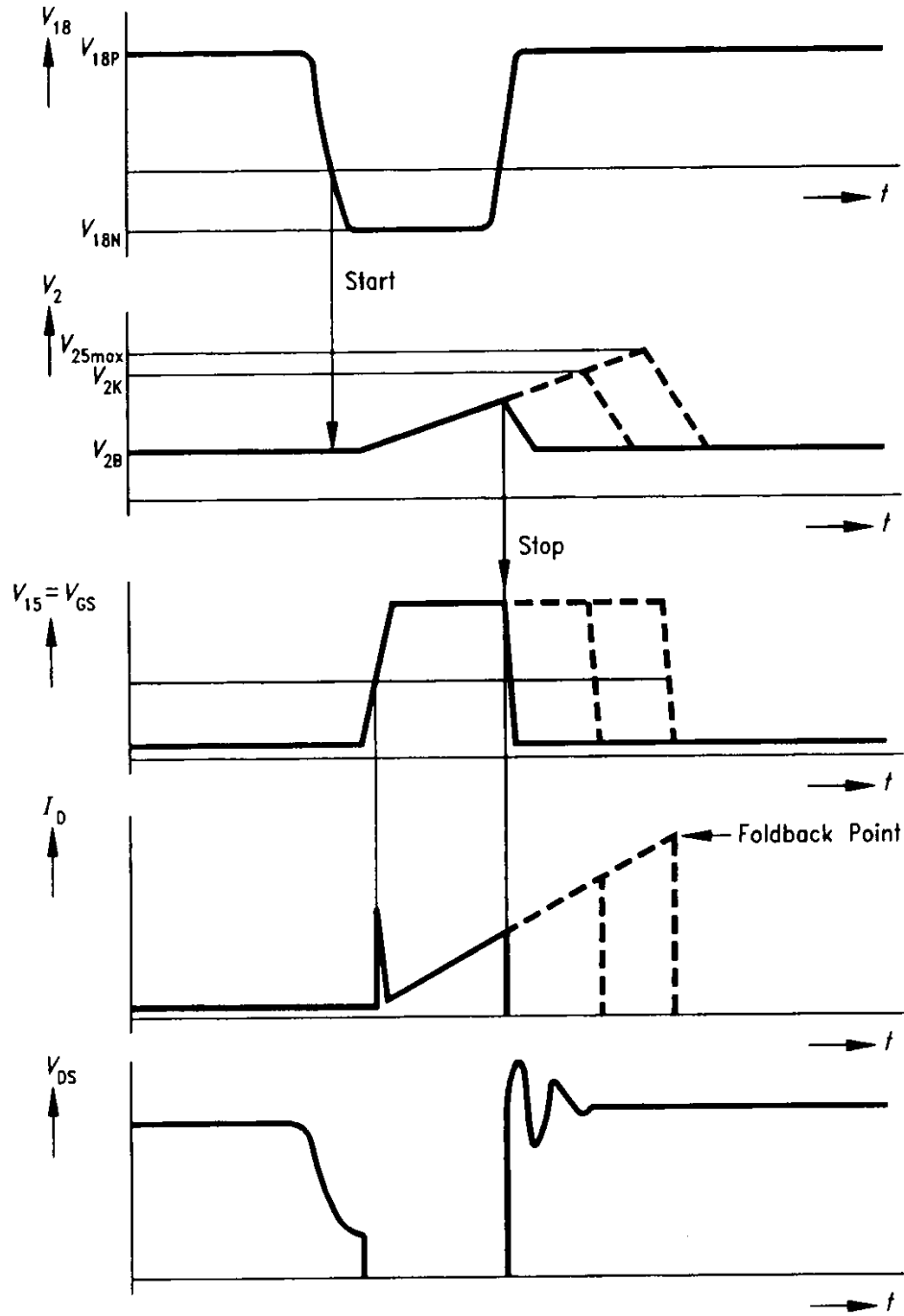
Test Circuit 2



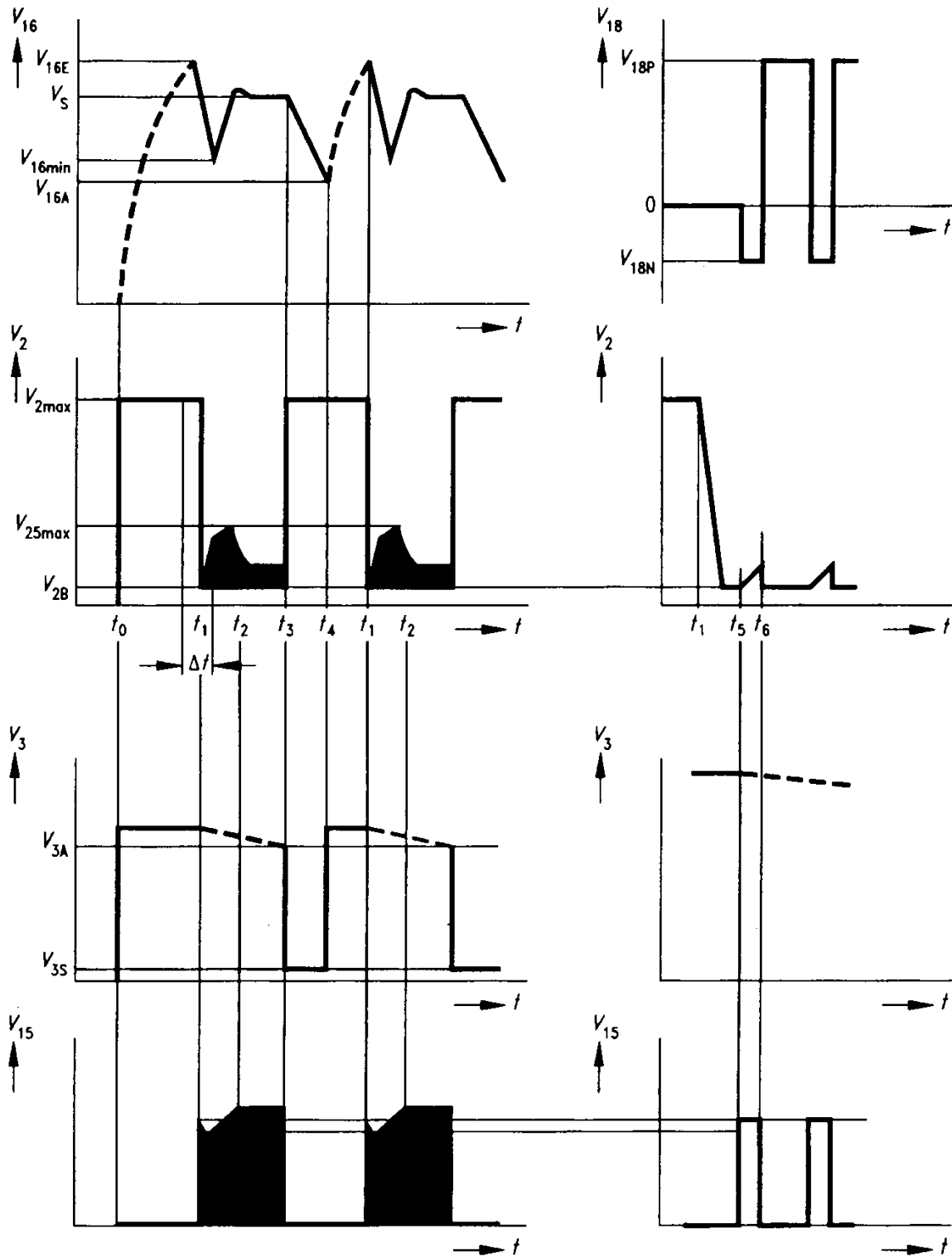


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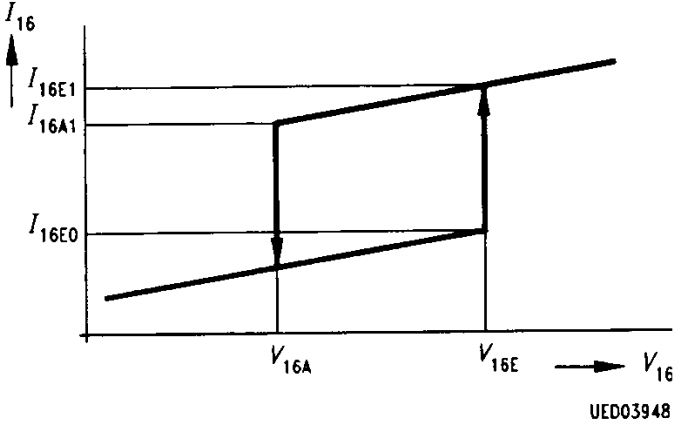
Application Circuit



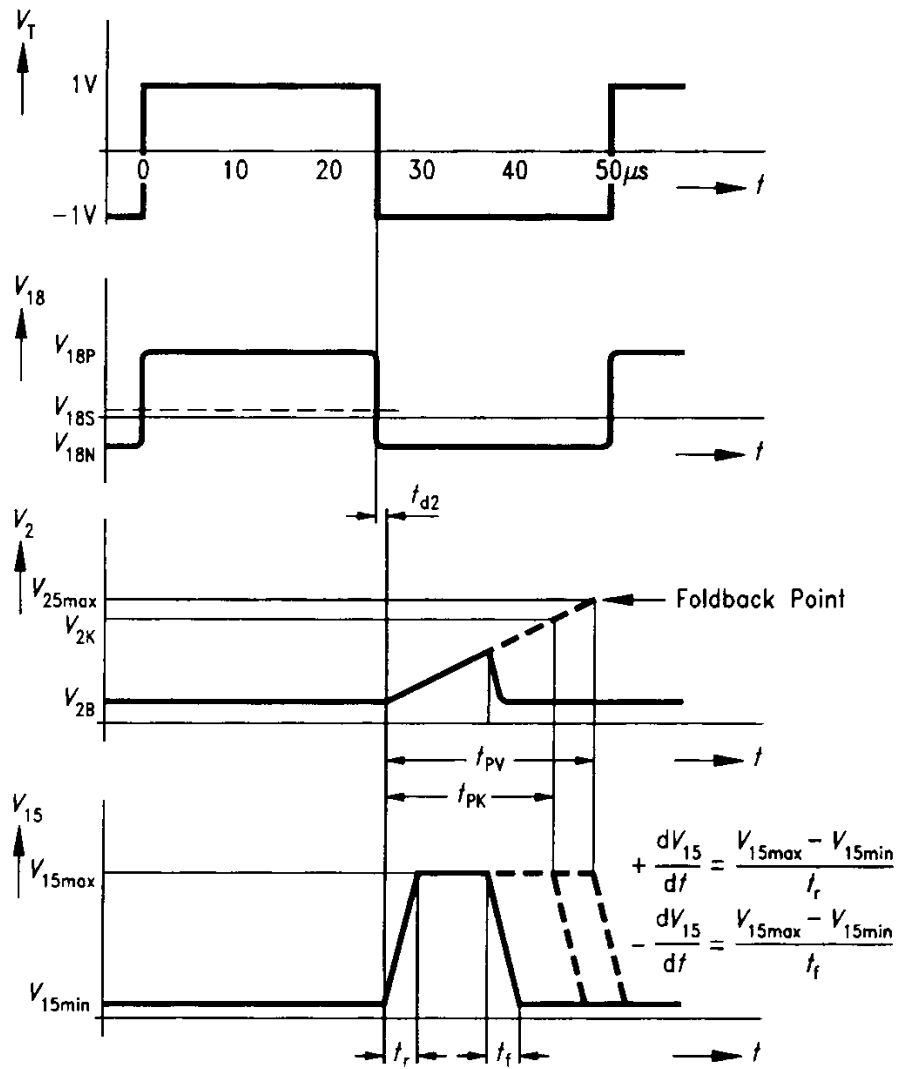
UED03869



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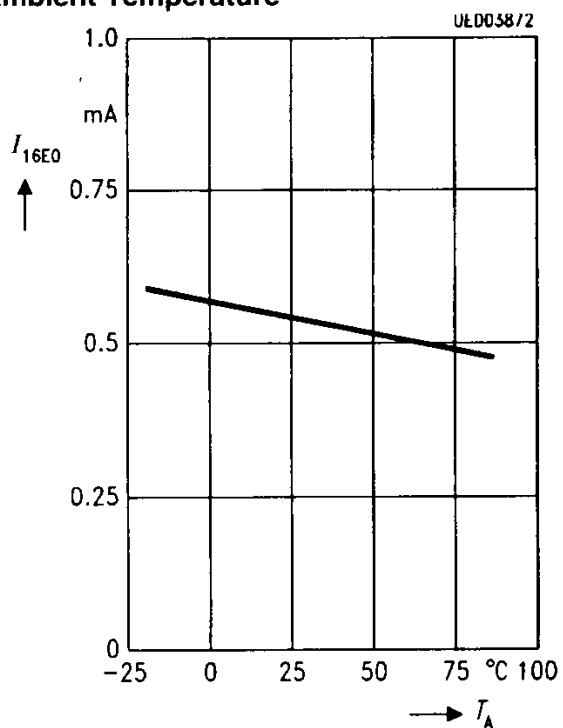
Start-Up Hysteresis



UED03871

Operation in Test Circuit 2

Start-Up Current as a Function of the Ambient Temperature



Overload Point Correction as a Function of the Voltage at Pin 3

